

A LATERALLY DIFFUSED METAL OXIDE
SEMICONDUCTOR DEVICE AND A METHOD OF MANUFACTURE THEREFOR

ABSTRACT OF THE DISCLOSURE

A laterally diffused metal oxide semiconductor (LDMOS) device
5 and a method of manufacture therefor. The method of manufacturing
the LDMOS device includes forming an amorphous region in a
semiconductor substrate between isolation structures and adjacent
a gate structure, by implanting an amorphizing element, such as
silicon or germanium, in the semiconductor substrate. The method
10 further includes diffusing a first source/drain dopant laterally in
the amorphous region to form a first portion of a channel.